



SANYO Semiconductors

DATA SHEET

MOSFET : N-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

SCH2825 — General-Purpose Switching Device Applications

Features

- Composite type with a N-Channel Silicon MOSFET and a Schottky Barrier Diode contained in one package facilitating high-density mounting.
- [MOSFET]
 - Low ON-resistance.
 - Ultrahigh-speed switching.
 - 4V drive.
- [SBD]
 - Short reverse recovery time.
 - Low forward voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		1.6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycles≤1%	6.4	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² ×0.8mm) 1unit	0.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _R RM		30	V
Nonrepetitive Peak Reverse Surge Voltage	V _R S		30	V
Average Output Current	I _O		0.5	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	3	A
Junction Temperature	T _J		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : XA

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SCH2825

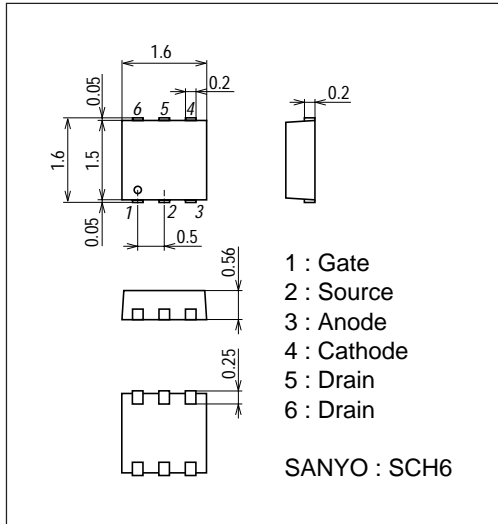
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=800mA$	0.6	1.0		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=800mA, V_{GS}=10V$		135	180	$m\Omega$
	$R_{DS(on)2}$	$I_D=400mA, V_{GS}=4V$		230	330	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		88		pF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		19		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		11		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		3.4		ns
Rise Time	t_r	See specified Test Circuit.		3.5		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		10.6		ns
Fall Time	t_f	See specified Test Circuit.		4.0		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=1.6A$		2.0		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=1.6A$		0.33		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=1.6A$		0.29		nC
Diode Forward Voltage	V_{SD}	$I_S=1.6A, V_{GS}=0V$		0.82	1.2	V
[SBD]						
Reverse Voltage	V_R	$I_R=0.5mA$	30			V
Forward Voltage	V_F	$I_F=0.5A$		0.42	0.48	V
Reverse Current	I_R	$V_R=15V$			120	μA
Interterminal Capacitance	C	$V_R=10V, f=1MHz$		13		pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=100mA$, See specified Test Circuit.			10	ns

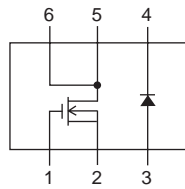
Package Dimensions

unit : mm (typ)

7028-003



Electrical Connection



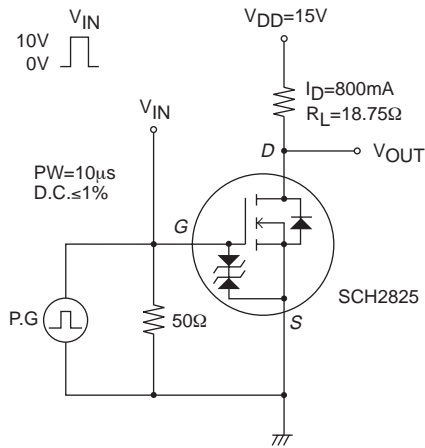
1 : Gate
2 : Source
3 : Anode
4 : Cathode
5 : Drain
6 : Drain

Top view

SCH2825

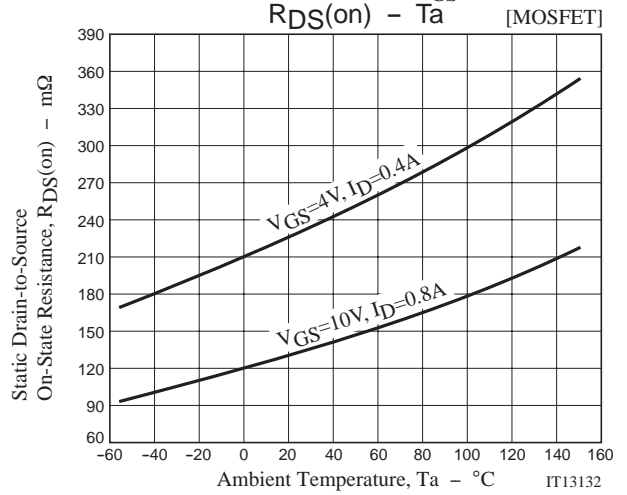
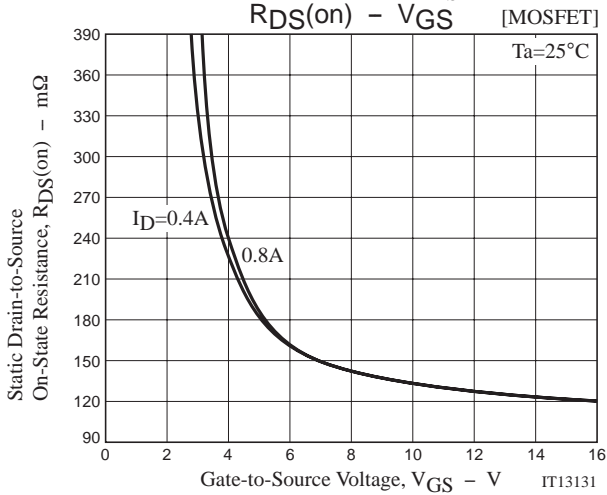
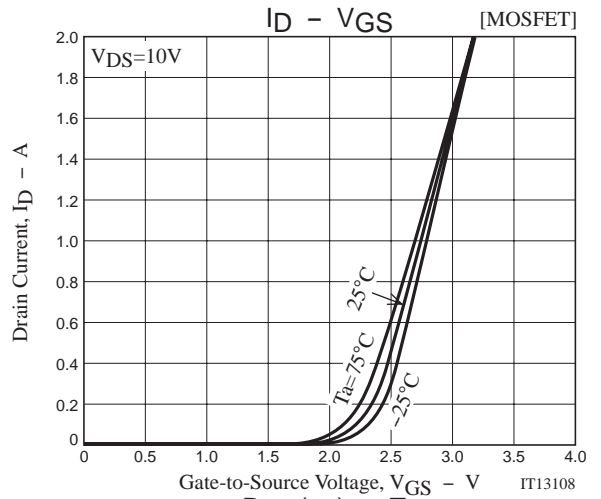
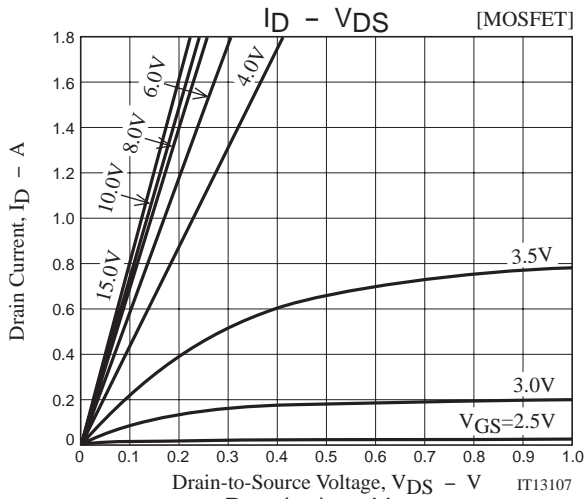
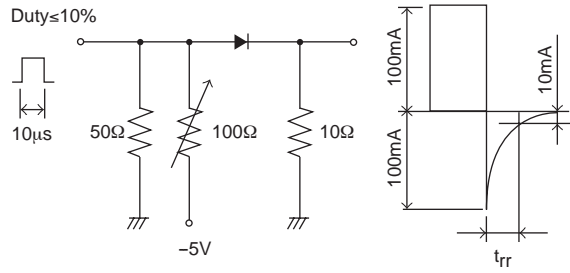
Switching Time Test Circuit

[MOSFET]

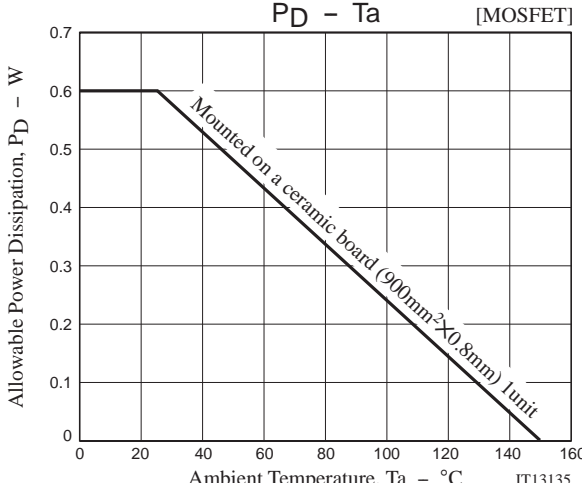
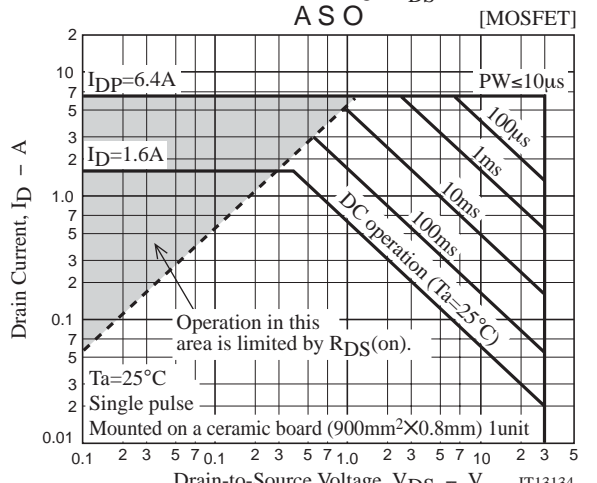
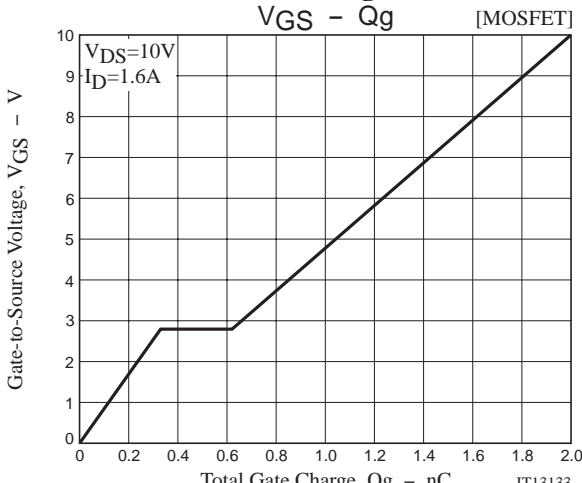
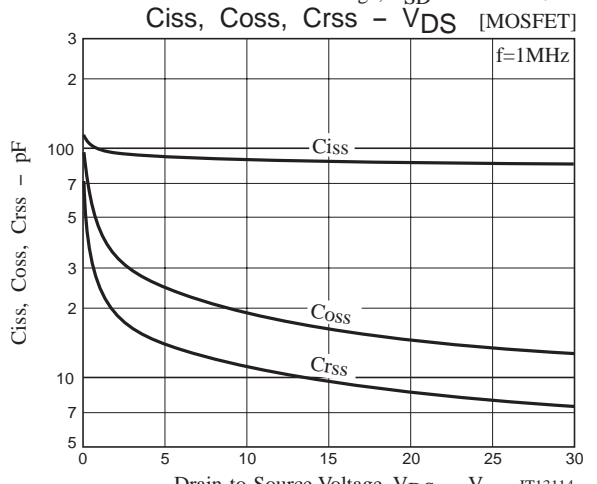
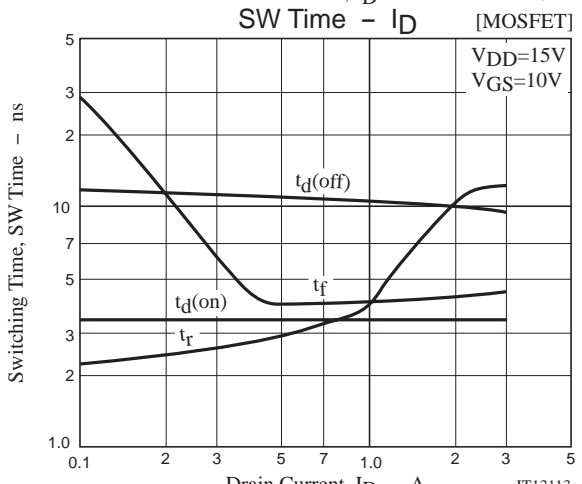
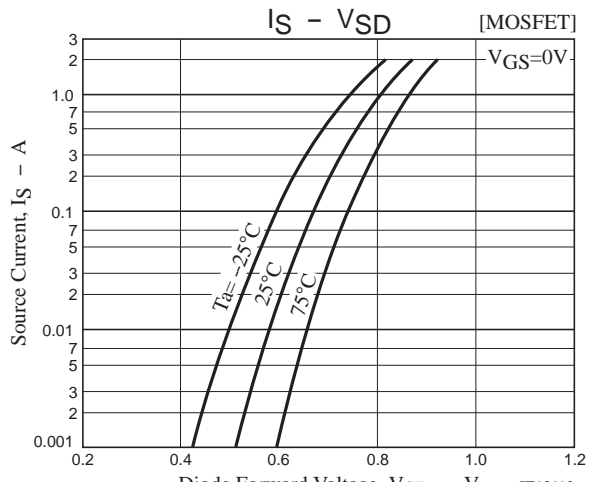
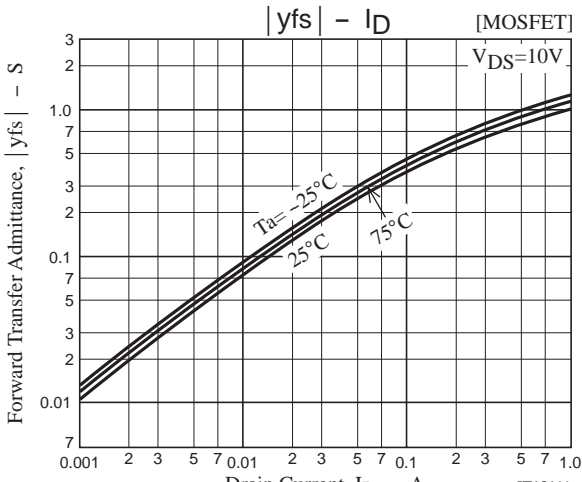


t_{rr} Test Circuit

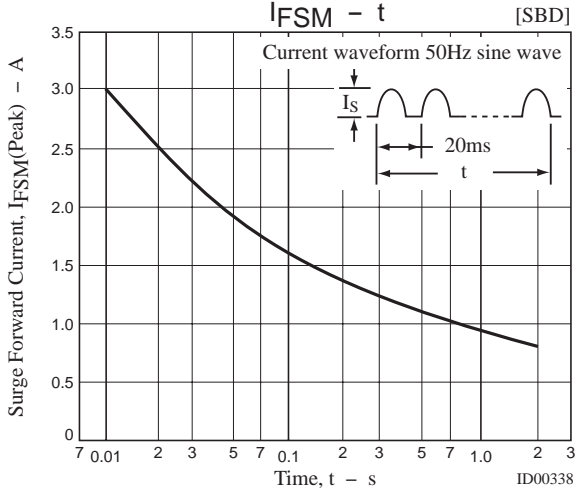
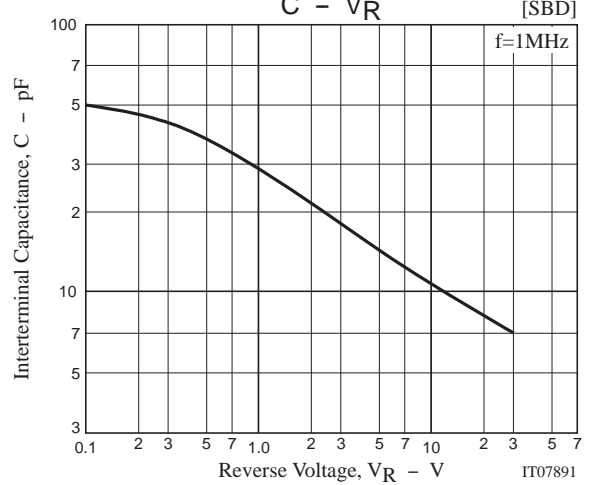
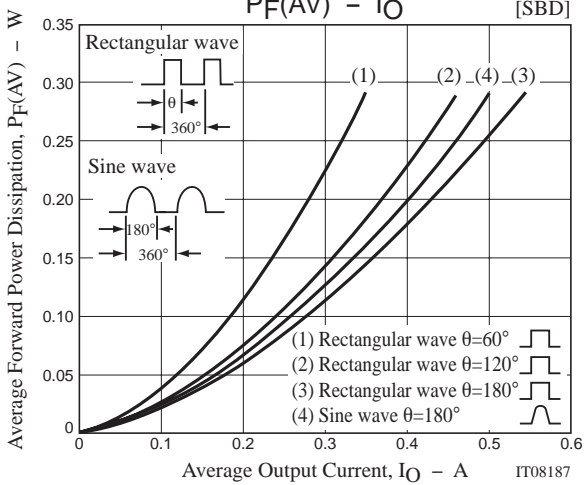
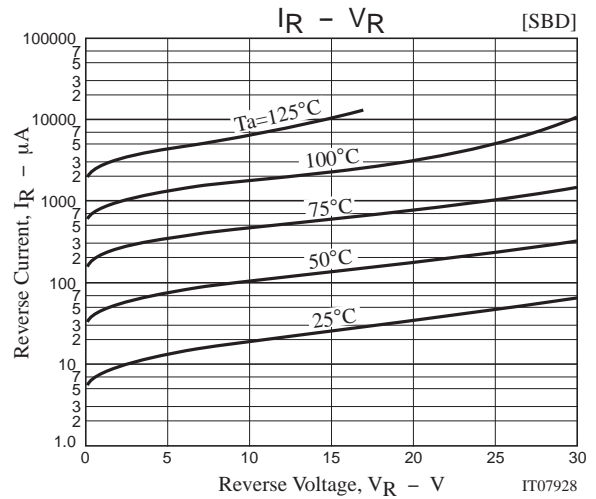
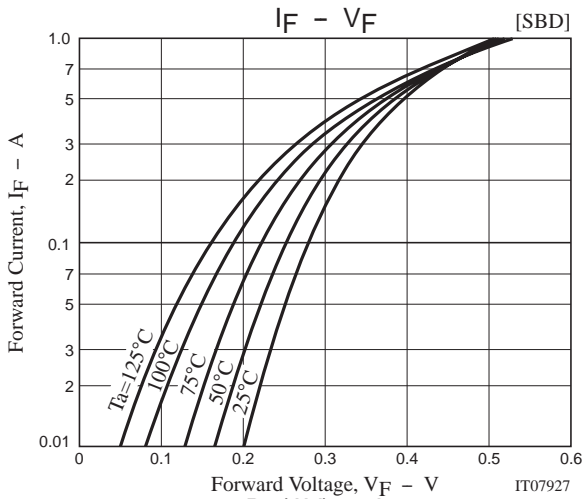
[SBD]



SCH2825



SCH2825



Note on usage : Since the SCH2825 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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